US 20220376709A1

(19) **United States**

(12) **Patent Application Publication** (10) **Pub. No.: US 2022/0376709 A1**

Wu et al. (43) **Pub. Date: Nov. 24, 2022**

(54) **FAILURE-TOLERANT ERROR CORRECTION LAYOUT FOR MEMORY SUB-SYSTEMS**

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(21) Appl. No.: **17/880,144**

(22) Filed: **Aug. 3, 2022**

Related U.S. Application Data

(63) Continuation of application No. 16/205,075, filed on Nov. 29, 2018, now Pat. No. 11,438,012.

Publication Classification

(51) **Int. Cl.**
H03M 13/15 (2006.01)
G06F 11/10 (2006.01)

(52) **U.S. Cl.**
CPC ***H03M 13/1525*** (2013.01); ***G06F 11/1076*** (2013.01)

(57) **ABSTRACT**

Codewords of an error correcting code can be received. The codewords can be separated into multiple segments. The segments of the codewords can be distributed in an error correcting layout across a plurality of dies where at least a portion of the error correcting (EC) layout constitutes a first layout in the form of a Latin Square.